

Art Unit: ***

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Claims 1-10 are canceled

11. (Amended) A polishing method according to claim 17, wherein said second polishing liquid does not contain abrasive grains.

12. (Amended) A polishing method according to claim 17, wherein said Ru compound is SrRuO_3 .

13. A polishing liquid for polishing a surface of a substrate containing Ru or a Ru compound in a surface region, wherein said polishing liquid contains

Art Unit: ***

tetravalent cerium ions and nitrate ions.

14. A polishing liquid according to claim 13, wherein said polishing liquid contains at least one kind of cerium compound selected from the group consisting of cerium (IV) nitrate and diammonium cerium (IV) nitrate.

15. A polishing liquid according to claim 13, wherein said polishing liquid does not contain abrasive grains.

16. A polishing liquid according to claim 13, wherein said Ru compound is SrRuO_3 .

17. (Twice Amended) A polishing method comprising:

preparing a first polishing liquid containing tetravalent cerium ions in a first concentration;

Art Unit: ***

adding a solvent for dilution to said first polishing liquid to form a second polishing liquid containing tetravalent cerium ions in a second concentration lower than the first concentration;

polishing a surface of a substrate containing Ru or a Ru compound in a surface region with the second polishing liquid,

wherein said addition of the solvent is carried out upon or immediately before the polishing of said substrate.

18. (New) A polishing method according to claim 17, wherein said second polishing liquid contains cerium (IV) nitrate in a concentration of 0.75% or more by weight.

19. (New) A polishing method according to claim 18, wherein said second polishing liquid contains cerium (IV) nitrate in a concentration of 0.75 to 2% by weight.

Art Unit: ***

20. (New) A polishing method according to claim 17, wherein said second polishing liquid contains diammonium cerium (IV) nitrate in a concentration of 3% or more by weight.

21. (New) A polishing method according to claim 20, wherein said second polishing liquid contains diammonium cerium (IV) nitrate in a concentration of 3 to 8% by weight.

22. (Amended) A polishing method comprising:
preparing a first polishing liquid containing cerium (IV) nitrate in a first concentration;
adding a solvent for dilution to said first polishing liquid to form a second polishing liquid containing cerium (IV) nitrate in a second concentration lower than the first concentration;
polishing a surface of a substrate containing Ru or a Ru compound in a surface region with the second polishing liquid,
wherein said adding of the solvent is carried out upon or immediately before the polishing of said substrate.

--23. (New) A polishing method according to claim 17, wherein said solvent has a property of dissolving a solute of said first polishing liquid and does not substantially contain any solute.

24. (New) A polishing method according to claim 17, wherein said solvent consists essentially of water.

Art Unit: ***

25. (New) A polishing method according to claim 22, wherein said solvent has a property of dissolving a solute of said first polishing liquid and does not substantially contain any solute.

26. (New) A polishing method according to claim 22, wherein said solvent consists essentially of water.--